2SA1952

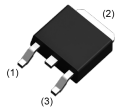
High-speed Switching Transistor (-60V,-5A)

Datasheet

Parameter	Value
V_{CEO}	-60V
I_C	-5A

●Outline

CPT

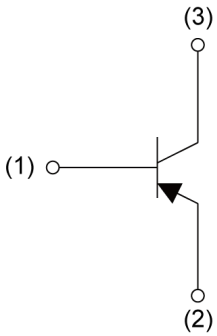


2SA1952
SOT-428

●Features

1)High speed switching.
2)Low $V_{CE(sat)}$
(Max. -0.3V at I_C/I_B=-3/-0.15A)
3)Wide SOA. (safe operating area)
4)Complements the 2SC5103.

●Inner circuit



(1) Base
(2) Emitter
(3) Collector

●Application

HIGH SPEED SWITCHING

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SA1952	CPT	6595	TL	330	16	2500	A1952

●Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	-100	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-5	A
	I_{CP}*1	-10	A
Power dissipation	P_D*2	1	W
	P_D*3	10	W
Junction temperature	T_j	150	℃
Range of storage temperature	T_{stg}	-55 to +150	℃

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter voltage	$V_{CEO(SUS)}$	I_C = -3A, I_B = -300mA L = 1mH	-60	−	−	V
Collector-base breakdown voltage	BV_{CBO}	I_C = -50μA	-100	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA	-60	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -50μA	-5	-	-	V
Collector cut-off current	I_{CBO}	V_{CB} = -100V	-	-	-10	μA
Emitter cut-off current	I_{EBO}	V_{EB} = -5V	-	-	-10	μA
Collector-emitter saturation voltage	$V_{CE(sat)}1$	I_C = -3A, I_B = -150mA	-	-	-300	mV
	$V_{CE(sat)}2$*4	I_C = -4A, I_B = -200mA	-	-	-500	mV
Base-emitter saturation voltage	$V_{BE(sat)}1$*4	I_C = -3A, I_B = -150mA	-	-	-1.2	V
	$V_{BE(sat)}2$*4	I_C = -4A, I_B = -200mA	-	-	-1.5	V
DC current gain	$h_{FE}1$*4	V_{CE} = -2V, I_C = -1A	82	150	270	-
	$h_{FE}2$*4	V_{CE} = -2V, I_C = -3A	40	-	-	
Transition frequency	f_T*4	V_{CE} = -10V, I_E = 0.5A, f = 30MHz	-	80	-	MHz
Output capacitance	C_{ob}	V_{CB} = -10V, I_E = 0A, f = 1MHz	-	130	-	pF
Turn-on delay time	t_{on}	I_C = -3A, I_{B1} = -150mA, I_{B2} = 150mA, V_{CC} ≃ -30V, R_L = 10Ω See test circuit	-	-	0.3	μs
Storage time	t_{stg}		-	-	1.5	μs
Fall time	t_f		-	-	0.3	μs

hFE values are calssified as follows :

rank	P	Q	-	-	-
$h_{FE}1$	82-180	120-270	-	-	-

*1 t=100ms

*2 Ta=25℃

*3 Tc=25℃

*4 Pulsed

●Electrical characteristic curves(T_a = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

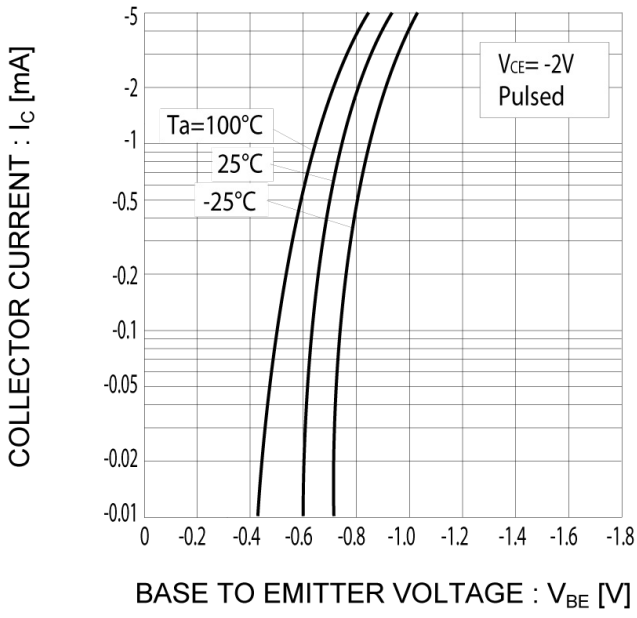


Fig.2 Typical Output Characteristics

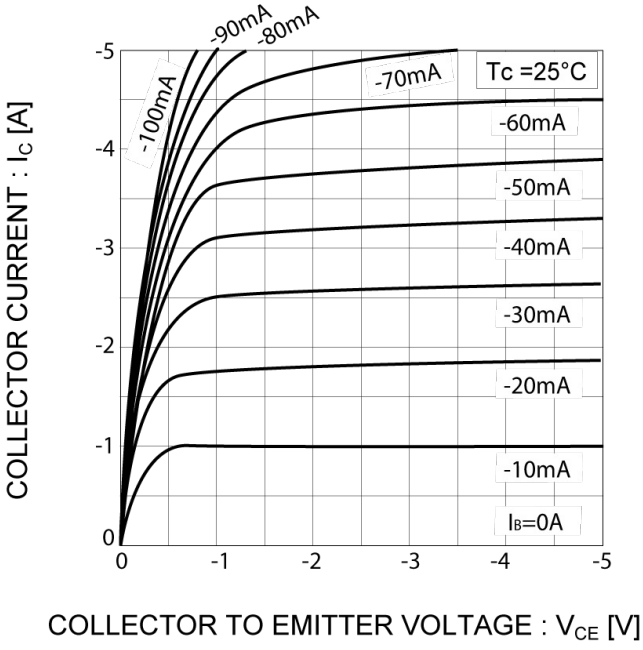


Fig.3 DC Current Gain vs. Collector Current (I)

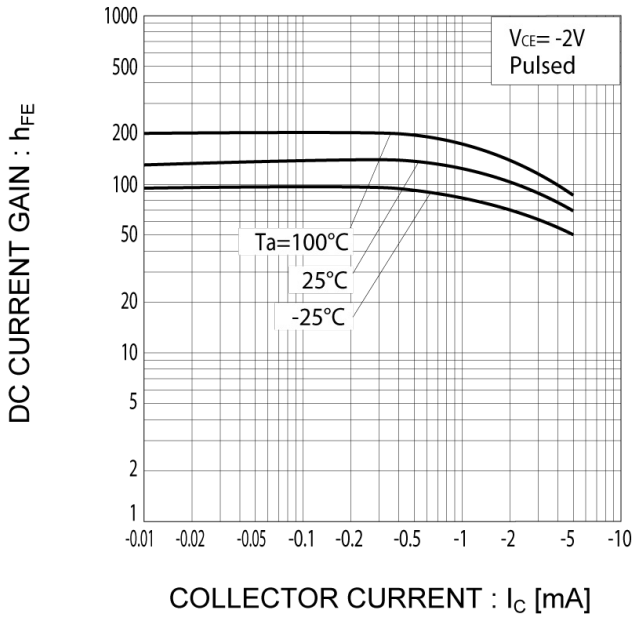
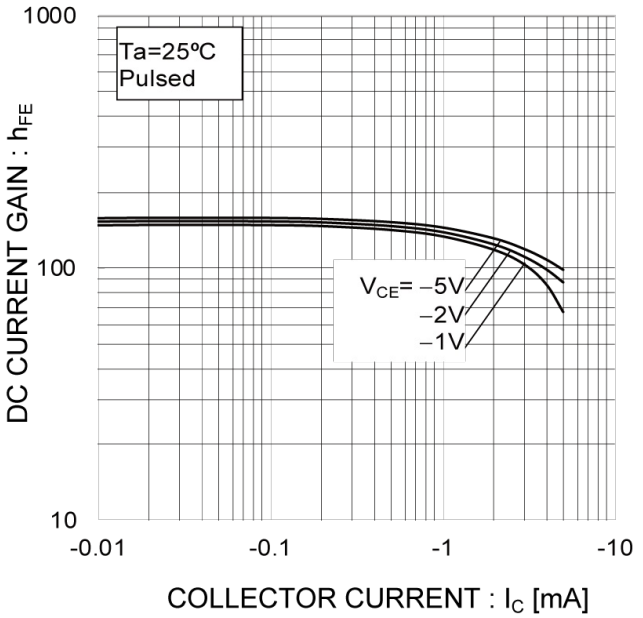


Fig.4 DC Current Gain vs. Collector Current (II)



●Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

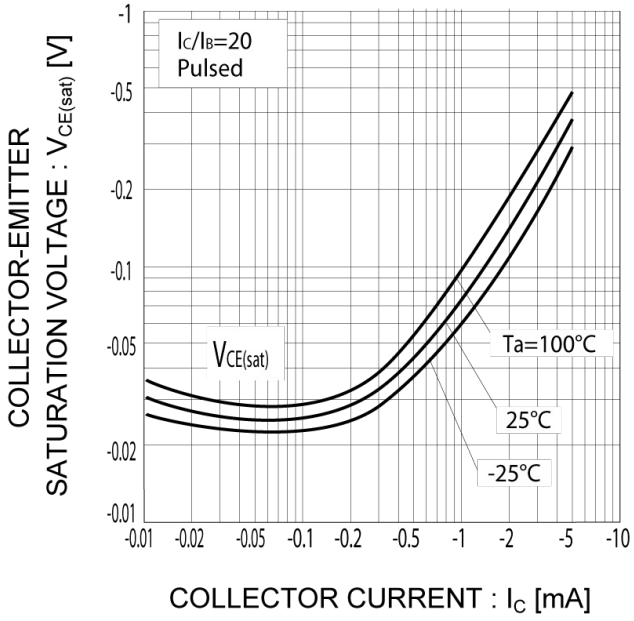


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

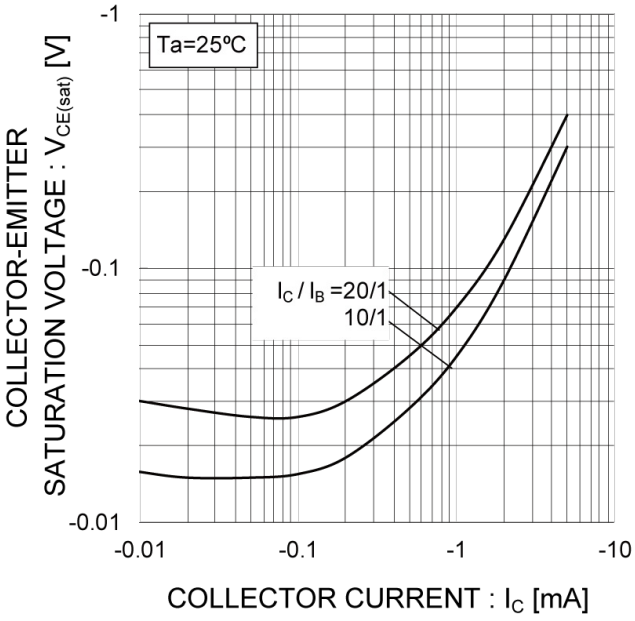


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

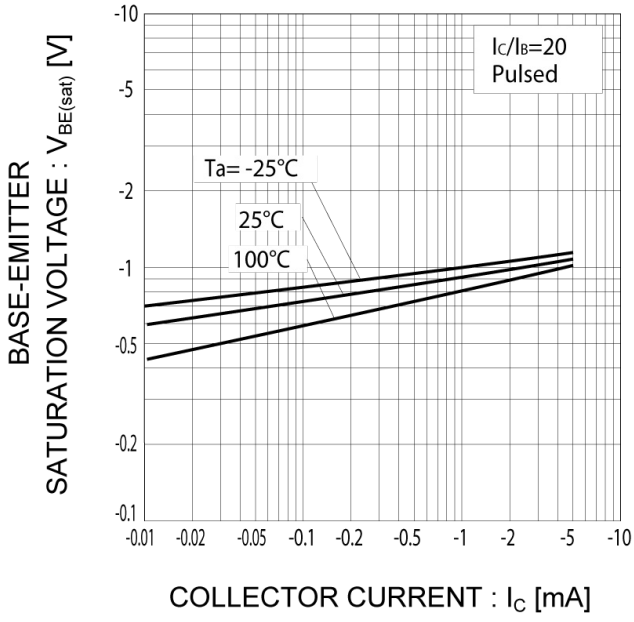
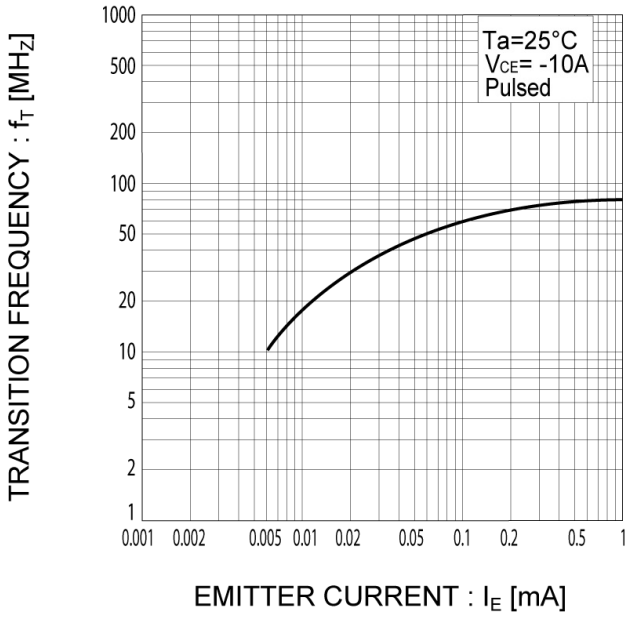


Fig.8 Gain Bandwidth Product vs. Emitter Current



●Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter Input Capacitance vs. Emitter-Base Voltage
Collector Output Capacitance vs. Collector-Base Voltage

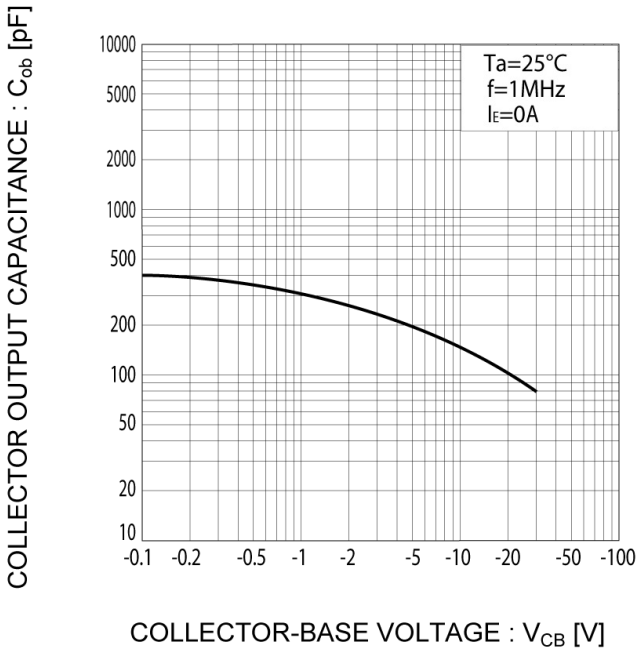
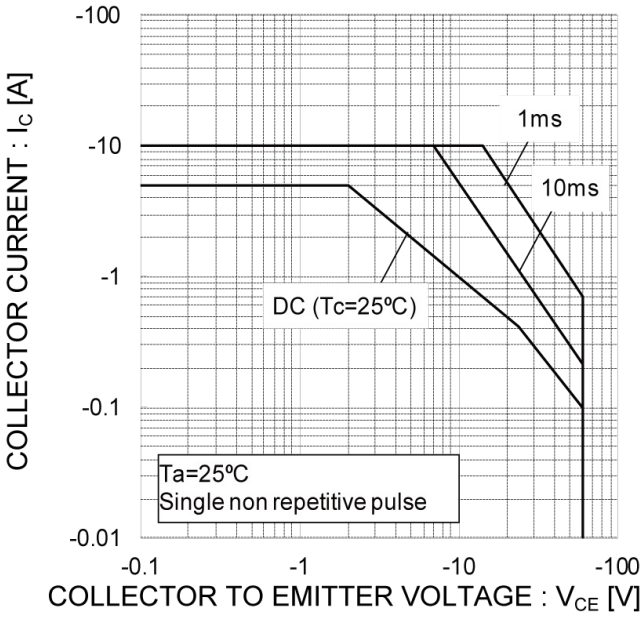
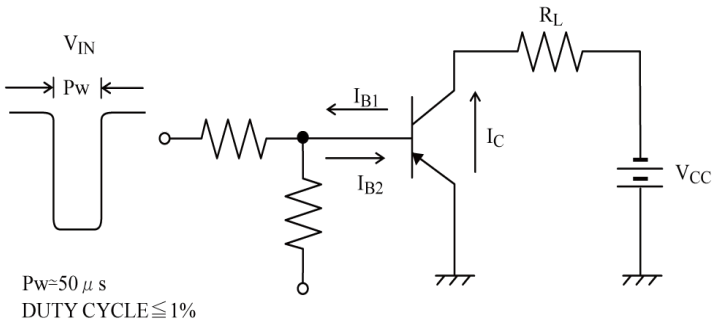
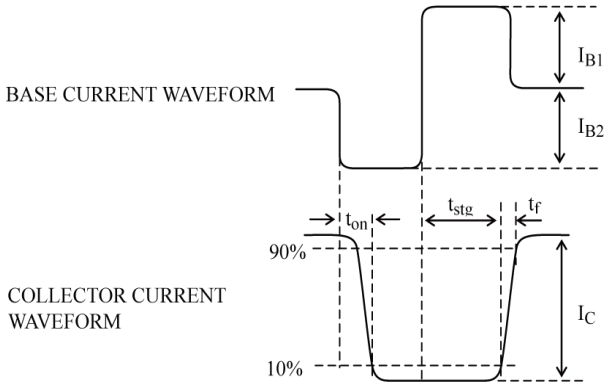


Fig.10 Safe Operating Area



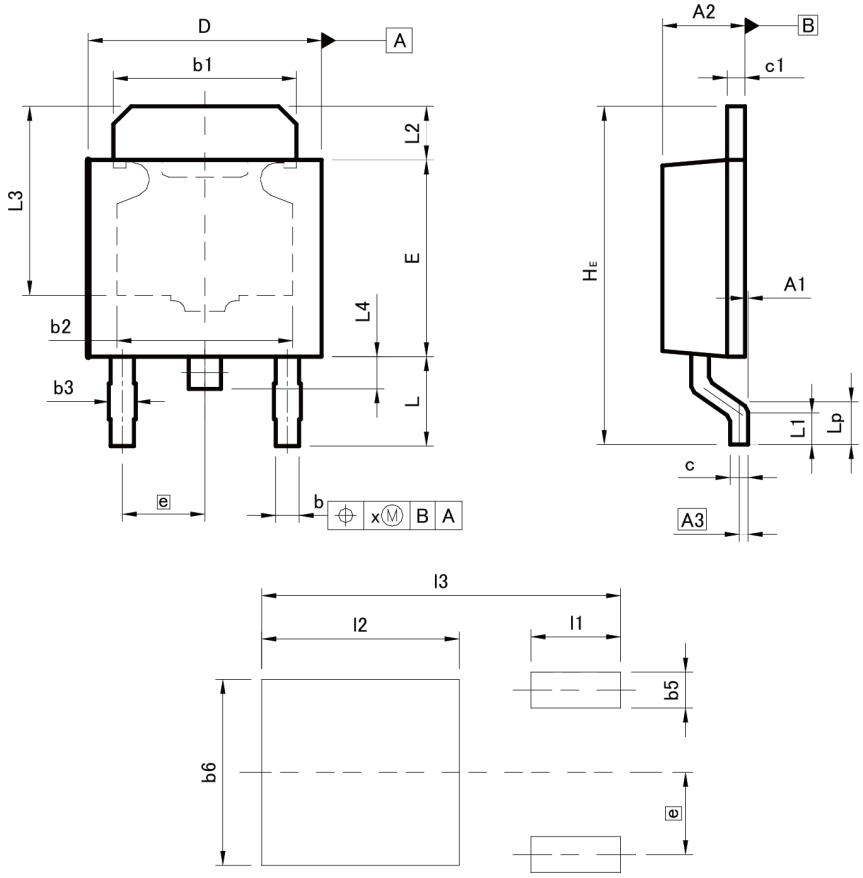
SWITCHING TIME TEST CIRCUIT





●Dimensions

CPT



Pattern of terminal position areas
[Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.15	0.000	0.006
A2	2.20	2.50	0.087	0.098
A3	0.25		0.010	
b	0.55	0.75	0.022	0.030
b1	5.00	5.30	0.197	0.209
b2	5.00		0.197	
b3	0.75		0.030	
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
E	5.40	5.80	0.213	0.228
e	2.30		0.091	
HE	9.00	10.00	0.354	0.394
L	2.20	2.80	0.087	0.110
L1	0.80	1.40	0.031	0.055
L2	1.20	1.80	0.047	0.071
L3	5.30		0.209	
L4	0.90		0.035	
Lp	1.00	1.60	0.039	0.063
x	–	0.25	–	0.010

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	–	1.00	–	0.04
b6	–	5.20	–	0.205
l1	–	2.50	–	0.098
l2	–	5.50	–	0.217
l3	–	10.00	–	0.394

Dimension in mm/inches

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.

6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.

7) The Products specified in this document are not designed to be radiation tolerant.

8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.

9) Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.

10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.

11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.

12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.

13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.

14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.

ROHM SEMICONDUCTOR

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor:

2SA1952TLQ